SSC8LA26GS6A

N-Channel Enhancement Mode MOSFET

➢ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$ Typ.	I_D
100V	±20V	79mΩ@10V	4A
		100mΩ@4V5	

➢ Description

The SSC8LA26GS6A is N-Channel enhancement mode MOSFET. Uses SGT Technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC - DC conversion, power switch and charging circuit.

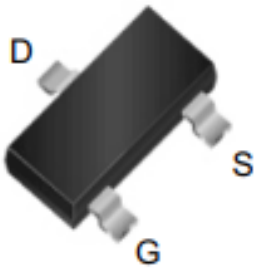
➢ Applications

- ➢ Inverter
- ➢ DC-DC Converter
- ➢ Half and Full Bridge Topology
- ➢ Motor Drive Control

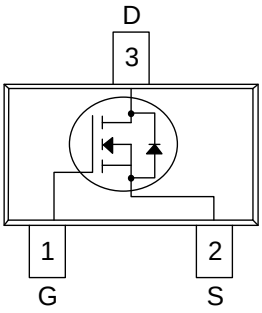
➢ Ordering Information

Device	Package	Shipping
SSC8LA26GS6A	SOT-23-3L	3000/Reel

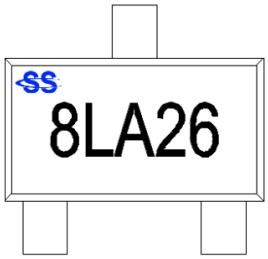
➢ Pin configuration



SOT-23-3L



Pin Configuration (Top View)



Marking

➢ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	100	V
V_{GSS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current [a]	4	A
I_{DM}	Pulsed Drain Current [b]	16	A
P_D	Power Dissipation [c]	1.6	W
T_J	Operation junction temperature	-55~150	℃
T_{STG}	Storage temperature range	-55~150	℃

➢ Thermal Resistance Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance [a]	85	℃/W

Note:

a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz.copper, in a still air environment with T_A=25℃.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.

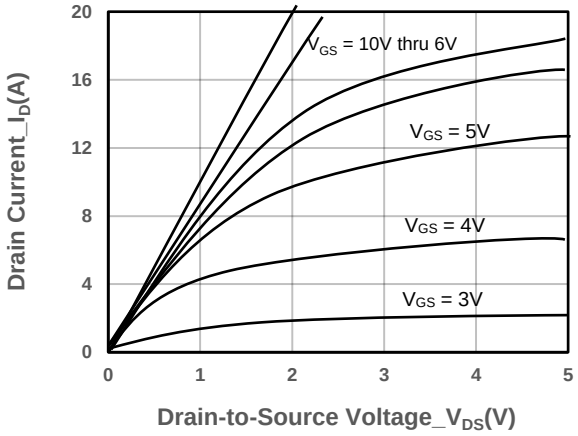
b. Repetitive rating, pulse width limited by junction temperature.

c. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

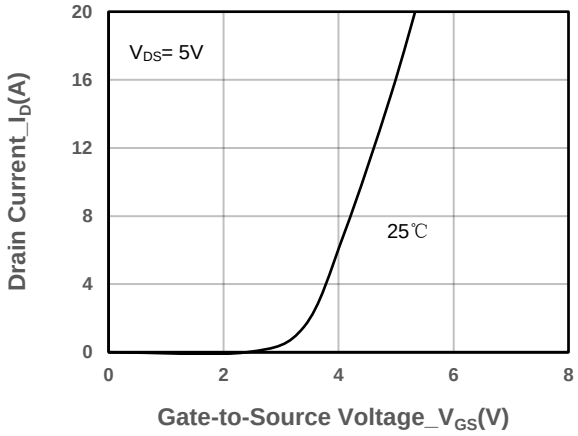
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250uA	1.2	1.8	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 4A		79	100	mΩ
		V_{GS} = 4.5V, I_D = 2A		100	125	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =100V, V_{GS} = 0V			1	μA
Gate-Source Leak Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Transconductance	G_{FS}	V_{DS} = 5V, I_D = 4A		8.0		s
Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = 4A		0.7	1.3	V
Input Capacitance	C_{ISS}	V_{DS} = 50V, V_{GS} = 0V, f = 1MHz		190		pF
Output Capacitance	C_{OSS}			47		
Reverse Transfer Capacitance	C_{RSS}			5.4		
Turn-on Delay Time	$T_{D(ON)}$	V_{GS} = 10V, I_D = 4A V_{DS} = 50V, R_G = 3Ω		8.9		ns
Rise Time	T_r			3.0		
Turn-off Delay Time	$T_{D(OFF)}$			13		
Fall Time	T_f			5.0		
Total Gate Charge	Q_G	V_{GS} = 10V, V_{DS} = 50V, I_D = 4A		4.0		nC
Gate to Source Charge	Q_{GS}			1.0		
Gate to Drain Charge	Q_{GD}			1.1		
Diode Recovery Time	T_{rr}	I_F=4A, di/dt=100A/us		17		ns
Diode Recovery Charge	Q_{rr}	I_F=4A, di/dt=100A/us		11		nC

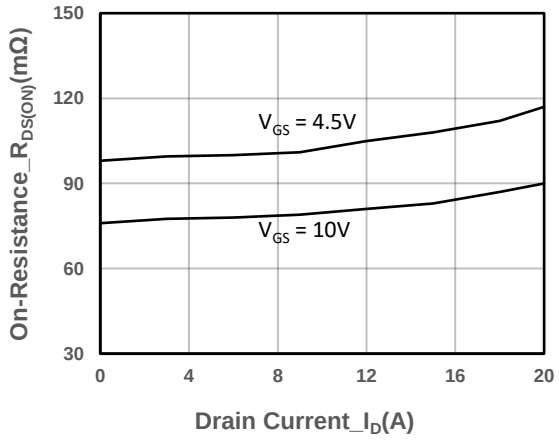
➢ Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



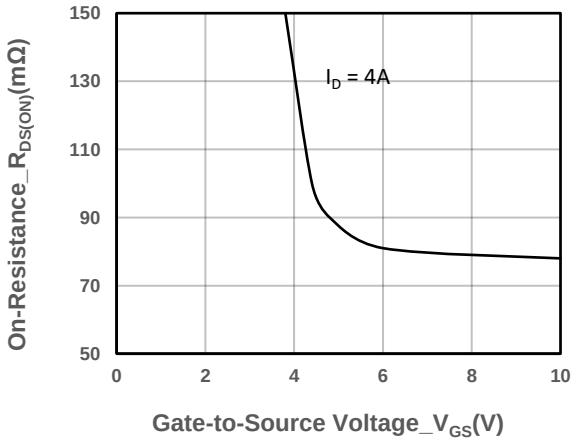
Output Characteristics



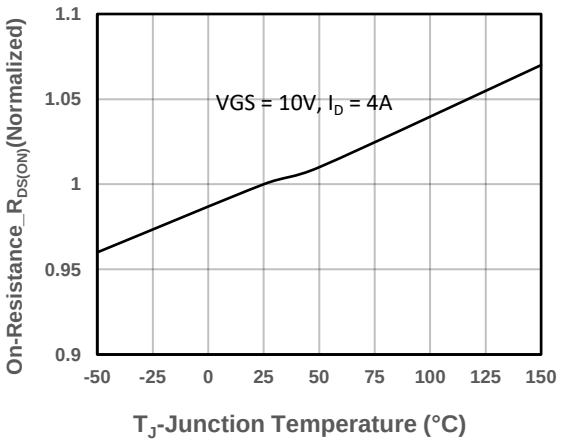
Transfer Characteristics



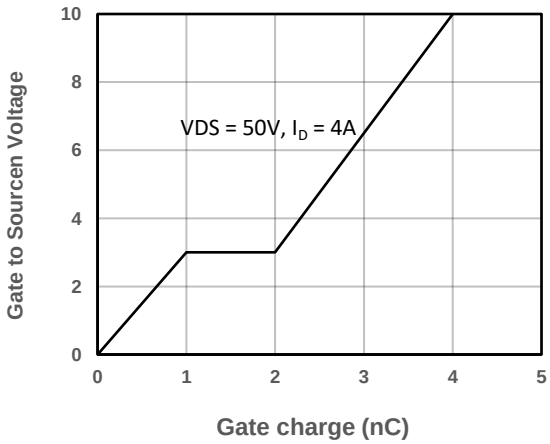
On-Resistance vs. Drain Current and Gate Voltag



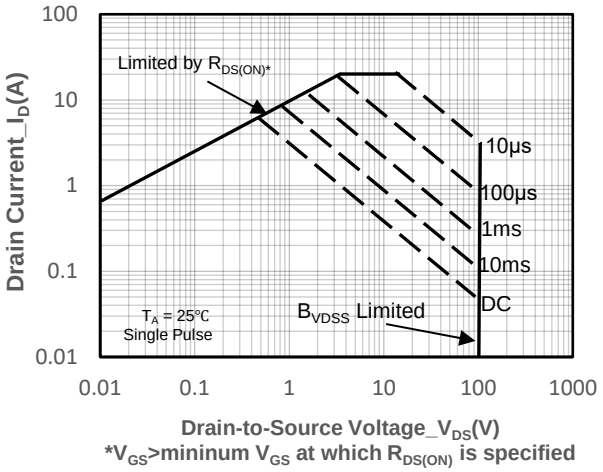
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature

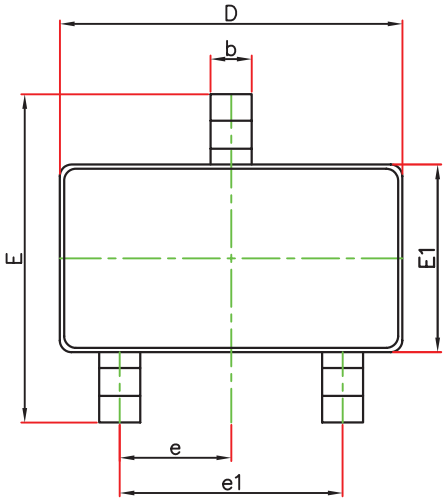


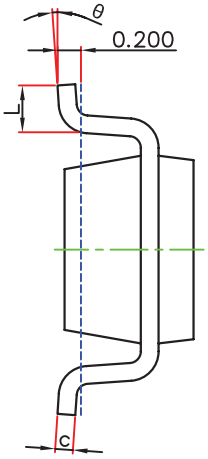
Gate-Source Voltage vs. Gate charge

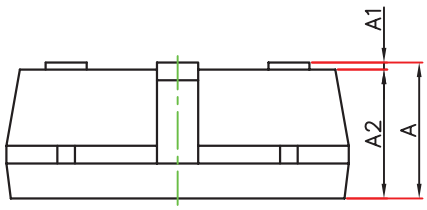


Safe Operating Area vs. Junction-to-Ambient

➢ Package Information

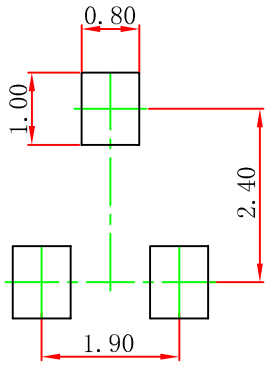






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

➢ Recommended Pad outline (Unit: mm)



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